

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	583	438/199.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 07:25
L2	855	438/199.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 07:41
L3	150	438/288.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 07:47
L4	1468	438/118.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 08:09
L5	351	438/406.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 08:27
L6	203	438/409.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 08:33
L7	5	438/409.ccls. and diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 08:35
L8	1046	438/455.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 08:53
L9	239	438/456.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 08:56
L10	711	438/458.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 09:14

L11	73	438/531.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 09:26
L12	708	438/974.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 09:26
S1	686	molecular bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/27 11:44
S2	0	molecular bonding and atypical surface	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/09 17:30
S3	45	molecular bonding and rough	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/09 17:31
S4	52	diamond substrate and bonding layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 16:34
S5	0	diamond substrate and molecular bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/10 11:55
S6	473	diamond substrate and bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/10 11:55
S7	55	silicon nitride and molecular bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/10 12:09
S8	20	aluminum nitride and molecular bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/10 12:13
S9	319	aluminum nitride and bonding layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/10 12:30
S10	28	aluminum nitride substrate and bonding layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/10 12:30

S11	96	("4800137" "5177668" "5482784" "6093969" "6164357" "4535219" "4761346" "5284725" "5405809" "5408121" "5739888" "5798293" "5923539" "6140205" "6146457" "6163075" "6215135" "6215135" "6249052" "4269321" "4326004" "4370190" "4409278" "4844758" "4863808" "4908685" "4917963" "5209798" "5217849" "5250760" "5260095" "5319243" "5389816" "5395644" "5403700" "5442229" "5547508" "5674600" "5681777" "5763952" "5789805" "5795619" "5801448" "5805563" "5817530" "5876852" "5914274" "5917157" "5962970" "5981059").pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/14 10:13
S12	0	("4800137" "5177668" "5482784" "6093969" "6164357" "4535219" "4761346" "5284725" "5405809" "5408121" "5739888" "5798293" "5923539" "6140205" "6146457" "6163075" "6215135" "6215135" "6249052" "4269321" "4326004" "4370190" "4409278" "4844758" "4863808" "4908685" "4917963" "5209798" "5217849" "5250760" "5260095" "5319243" "5389816" "5395644" "5403700" "5442229" "5547508" "5674600" "5681777" "5763952" "5789805" "5795619" "5801448" "5805563" "5817530" "5876852" "5914274" "5917157" "5962970" "5981059").pn. and molecular adj bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/14 10:13
S13	40	molecular bonding same silicon	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 10:42
S14	28	diamond substrate and wafer bonding	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 18:00
S15	2	bonding layer and wafer bonding and intermediate layer and diamond substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 18:44
S16	0	bonding layer and wafer bonding and intermediate layer and aluminum nitride substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 18:46

S17	18	bonding layer and wafer bonding and intermediate layer and substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 18:55
S18	2	bonding layer and wafer bonding and intermediate layer same silicon nitride and substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 18:57
S19	8	bonding layer same oxide and wafer bonding and intermediate layer and substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/14 19:00
S20	83	molecular adj bonding and (diamond or aluminum adj nitride)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 12:12
S21	65	molecular adj bonding and (inhibit or prevent or constrain or arrest or obstruct or hinder or impede or prohibit or suppress) and (diamond or aluminum adj nitride)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:56
S22	3	molecular adj bonding same (inhibit or prevent or constrain or arrest or obstruct or hinder or impede or prohibit or suppress) and (diamond or aluminum adj nitride)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:57
S23	73	molecular adj bonding same (inhibit or prevent or constrain or arrest or obstruct or hinder or impede or prohibit or suppress)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:58
S24	21	molecular adj bonding same (inhibit or prevent or constrain or arrest or obstruct or hinder or impede or prohibit or suppress) and substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:58
S25	24	molecular adj bonding and aluminum adj nitride	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 12:12